

Tofiq Mammadov

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2438758/publications.pdf>

Version: 2024-02-01

47
papers

571
citations

623734

14
h-index

713466

21
g-index

47
all docs

47
docs citations

47
times ranked

142
citing authors

#	ARTICLE	IF	CITATIONS
1	Synthesis and magnetic characterizations of $TlInS_2$ single crystals. <i>Journal of Physics and Chemistry of Solids</i> , 2019, 195, 1950149.	2.3	3
2	Neutron diffraction study of the crystal structure of $TlInSe_2$ at high pressure. <i>International Journal of Modern Physics B</i> , 2019, 33, 1950149.	2.0	19
3	High Pressure Raman Study of Layered Semiconductor $TlGaSe_2$. <i>Materials Science-Poland</i> , 2018, 36, 203-208.	1.0	18
4	Parametric resonance and photogalvanic currents in layered $TlGaSe_2$ crystals. <i>Physics of the Solid State</i> , 2017, 59, 457-462.	0.6	4
5	Photovoltaic currents and activity of structural defects in a ferroelectric semiconductor $TlInS_2$: La single crystal. <i>Physics of the Solid State</i> , 2016, 58, 716-722.	0.6	5
6	Identification of intrinsic deep level defects responsible for electret behavior in $TlGaSe_2$ layered semiconductor. <i>Physica B: Condensed Matter</i> , 2016, 483, 82-89.	2.7	13
7	Magnetodielectric effects in Co-implanted $TlInS_2$ and $TlGaSe_2$ crystals. <i>Phase Transitions</i> , 2016, 89, 568-577.	1.3	5
8	$TlInS_2$ phase diagram and electrical conductivity of solid solutions in the $TlInS_2$ - $TlGaTe_2$ system. <i>Inorganic Materials</i> , 2015, 51, 877-883.	0.8	0
9	Admittance and Permittivity in Doped Layered $TlGaSe_2$ Single Crystals. <i>Acta Physica Polonica A</i> , 2014, 125, 1267-1271.	0.5	0
10	Photoelectric activity of defects in La-doped layered $TlInS_2$ crystals. <i>Low Temperature Physics</i> , 2014, 40, 830-836.	0.6	7
11	Pyroelectric properties and structural defects of a layered $TlInS_2$ crystal doped with lanthanum. <i>Physics of the Solid State</i> , 2014, 56, 2028-2034.	0.6	8
12	Photoelectric activity of structural defects of a single crystal of the ferroelectric-semiconductor $TlInS_2$: La. <i>Physics of the Solid State</i> , 2014, 56, 1605-1609.	0.6	12
13	Magnetic properties of Co implanted $TlInS_2$ and $TlGaSe_2$ crystals. <i>Solid State Communications</i> , 2012, 152, 407-409.	1.9	7
14	Photodielectric effect in $TlInS_2$ activated by the La impurity. <i>Physics of the Solid State</i> , 2009, 51, 264-269.	0.6	13
15	Unusual memory effects in an incommensurate phase of the $TlInS_2$ ferroelectric semiconductor. <i>Physics of the Solid State</i> , 2009, 51, 568-576.	0.6	9
16	Effect of illumination on negative linear expansion of $TlGaSe_2$ layered crystals. <i>Journal of Physics and Chemistry of Solids</i> , 2008, 69, 2544-2547.	4.0	13
17	Structural phase transitions in Fe^{3+} -doped ferroelectric $TlGaSe_2$ crystal. <i>Solid State Communications</i> , 2008, 145, 539-544.	1.9	18
18	Effect of external fields on the memory effect of the incommensurate phase in the ferroelectric-semiconductor $TlGaSe_2$. <i>Physics of the Solid State</i> , 2008, 50, 108-117.	0.6	13

#	ARTICLE	IF	CITATIONS
19	Preparation, crystal structure, and electrical properties of thallium monosulfide in the vicinity of high-temperature phase transitions. <i>Physics of the Solid State</i> , 2006, 48, 2322-2327.	0.6	9
20	EPR spectra of Fe ³⁺ centers in layered TlGaSe ₂ single crystal. <i>Solid State Communications</i> , 2005, 133, 389-392.	1.9	14
21	Negative thermal expansion in the layered semiconductor TlGaSe ₂ . <i>Physica Status Solidi (B): Basic Research</i> , 2005, 242, 983-989.	1.5	17
22	The effect of impurities on the phase transitions in the ferroelectric semiconductors TlInS ₂ and TlGaSe ₂ . <i>Journal of Physics Condensed Matter</i> , 2005, 17, 1985-1993.	1.8	28
23	Thermal hysteresis and memory effects in TlGaSe ₂ crystal with incommensurate phase. <i>Phase Transitions</i> , 2005, 78, 413-419.	1.3	6
24	Thermal history and dielectric behavior in the incommensurate phase of TlGaSe ₂ . <i>Journal of Non-Crystalline Solids</i> , 2005, 351, 2809-2812.	3.1	8
25	EPR study of Fe ³⁺ centers in ternary layered TlInS ₂ single crystal. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2004, 1, 3567-3570.	0.8	4
26	Time relaxation of dielectric constant in the commensurate phase of TlGaSe ₂ . <i>Solid State Communications</i> , 2004, 129, 761-764.	1.9	14
27	Phase Relations and Properties of Phases in the TlGaSe ₂ -TlCoSe ₂ System. <i>Inorganic Materials</i> , 2003, 39, 680-682.	0.8	0
28	Memory effect in ferroelectric-semiconductor with incommensurate phase TlGaSe ₂ . <i>Solid State Communications</i> , 2003, 128, 25-28.	1.9	31
29	Dielectric susceptibility behaviour in the incommensurate phase of TlInS ₂ . <i>Physica B: Condensed Matter</i> , 2003, 334, 13-20.	2.7	23
30	Effect of lattice deformation and phase transitions on the electronic spectra of TlGaS ₂ , TlGaSe ₂ , and TlInS ₂ layered semiconductors. <i>Physics of the Solid State</i> , 2003, 45, 2242-2248.	0.6	5
31	Deformation effects in electronic spectra of the layered semiconductors TlGaS ₂ , TlGaSe ₂ and TlInS ₂ . <i>Journal of Physics Condensed Matter</i> , 2003, 15, 1291-1298.	1.8	32
32	Phase transitions and metastable states in TlGaSe ₂ . <i>Phase Transitions</i> , 2003, 76, 1057-1064.	1.3	22
33	Thermal expansion of single crystals of the layered compounds TlGaSe ₂ and TlInS ₂ . <i>Low Temperature Physics</i> , 2001, 27, 676-680.	0.6	16
34	Behavior of the layered crystals TlInS ₂ and TlGaSe ₂ near phase transitions in a static electric field. <i>Low Temperature Physics</i> , 2000, 26, 56-61.	0.6	28
35	Band Gap Variation in Mixed Crystals with TlSe ₂ -Type Crystal Structure. <i>Physica Status Solidi (B): Basic Research</i> , 1988, 147, K99.	1.5	9
36	Phase transitions and polytypes in $\hat{\Gamma}^2$ TlInS ₂ ferroelectric-semiconductor. <i>Ferroelectrics, Letters Section</i> , 1988, 8, 125-133.	1.0	7

#	ARTICLE	IF	CITATIONS
37	Electrical and pyroelectric properties of TlInS ₂ . Ferroelectrics, 1988, 83, 161-164.	0.6	5
38	Anomalous behaviour of the Urbach edge and phase transitions in TlGaSe ₂ . Solid State Communications, 1986, 58, 295-297.	1.9	28
39	Phase transitions under pressure and exciton-phonon interactions in Ga _x Se _{1-x} crystals. Solid State Communications, 1986, 59, 707-710.	1.9	1
40	Fundamental Absorption Edge of TlSe and TlInTe ₂ Crystals. Physica Status Solidi (B): Basic Research, 1985, 127, K55.	1.5	7
41	Influence of Hydrostatic Pressure on the Fundamental Absorption Edge of TlGaSe ₂ , TlGaS ₂ , and TlInS ₂ Crystals. Physica Status Solidi (B): Basic Research, 1985, 131, K23.	1.5	16
42	Phase transitions in the system of TlGa _x In _{1-x} Se ₂ S ₂ (1-x) solutions under hydrostatic pressure. Solid State Communications, 1985, 56, 989-993.	1.9	5
43	Phase transition and anisotropy of thermal expansion in TlInS ₂ . Solid State Communications, 1985, 53, 601-602.	1.9	24
44	The Influence of Hydrostatic Pressure on the Fundamental Absorption Edge of Crystals with TlSe ϵ Type Structure. Physica Status Solidi (B): Basic Research, 1984, 126, K139.	1.5	14
45	The Fundamental Absorption Spectra of TlInSe ₂ Crystals Under Pressure. Physica Status Solidi (B): Basic Research, 1983, 117, K109.	1.5	9
46	The Fundamental Absorption Edge of TlInSe ₂ . Physica Status Solidi (B): Basic Research, 1982, 113, K43.	1.5	16
47	Shift of the Fundamental Absorption Edge of TlSe Under Hydrostatic Pressure. Physica Status Solidi (B): Basic Research, 1982, 113, K127.	1.5	6